D³GaN - breaking the boundaries of EV inverter efficiency Hans Winter, VP Product, VisIC Technologies

GaN

Bodo's Wide Bandgap Event 2024 Making WBG Designs Happen

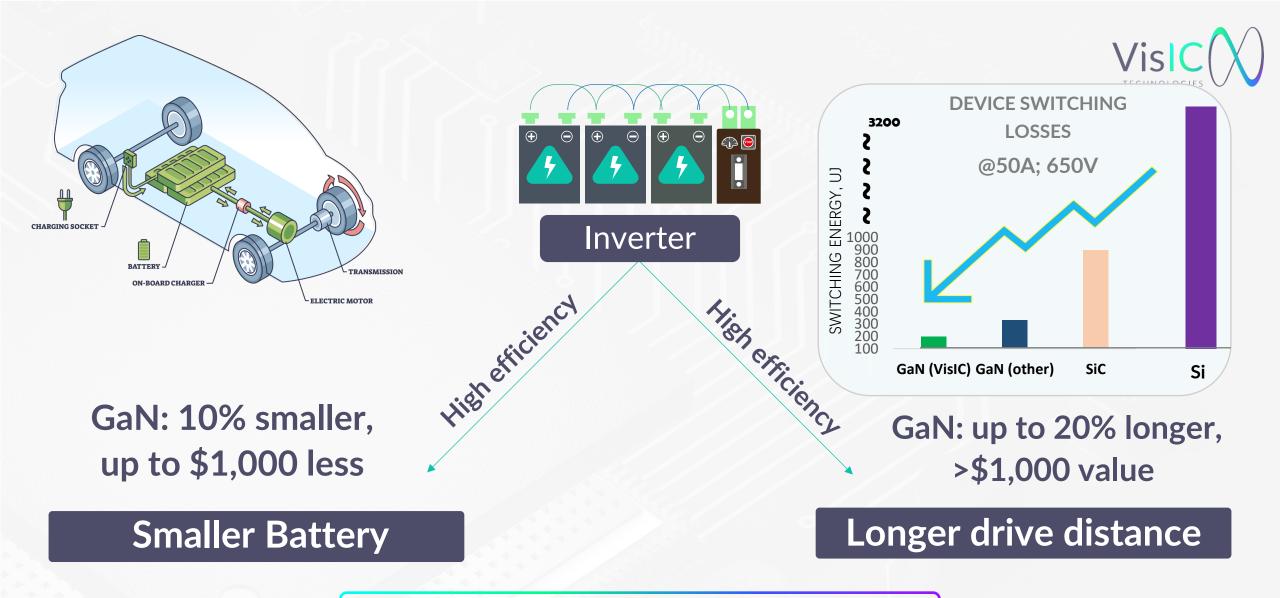




VisIC D³GaN Traction Inverters with SiC Performance @ Si Costs

lower vehicle cost, longer driving distances, better energy-efficiency

VisIC Technologies Ltd 2024

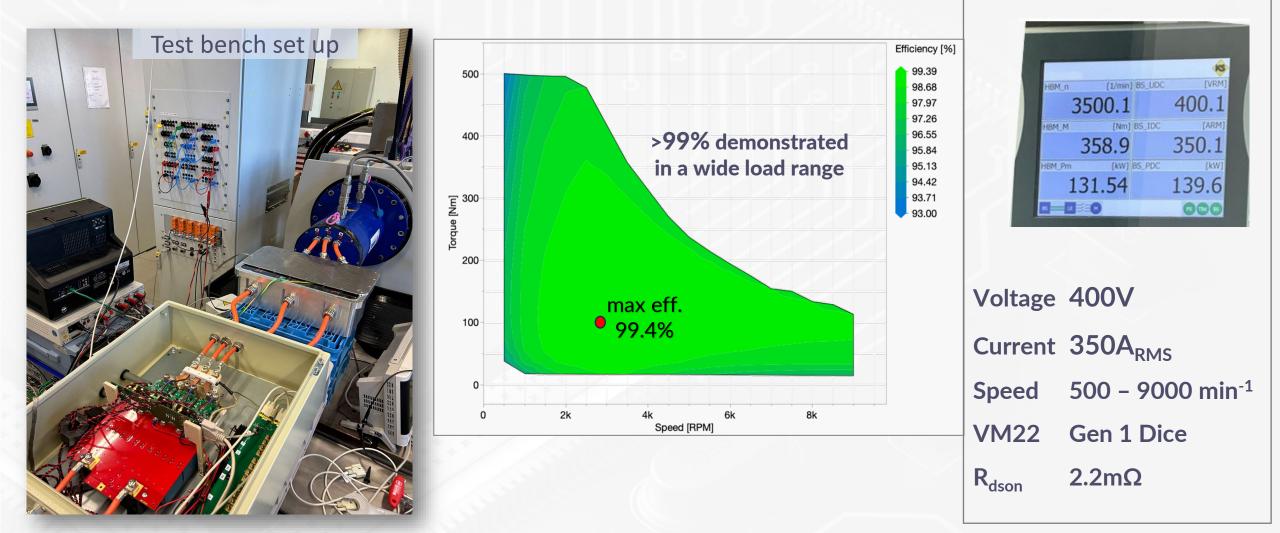


Reference to Tesla SiC \rightarrow 4% efficiency improvement \rightarrow 10% driving distance

VM022 Prototype tested at OEM test bench



VisIC D³GaN drives a 140kW e-Machine on OEM Test Bench



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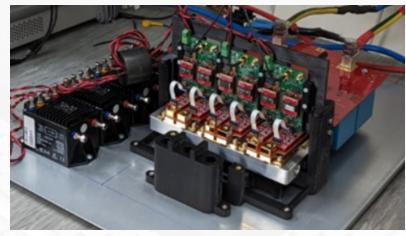
VM022 Prototype tested at OEM test bench Detailed results:

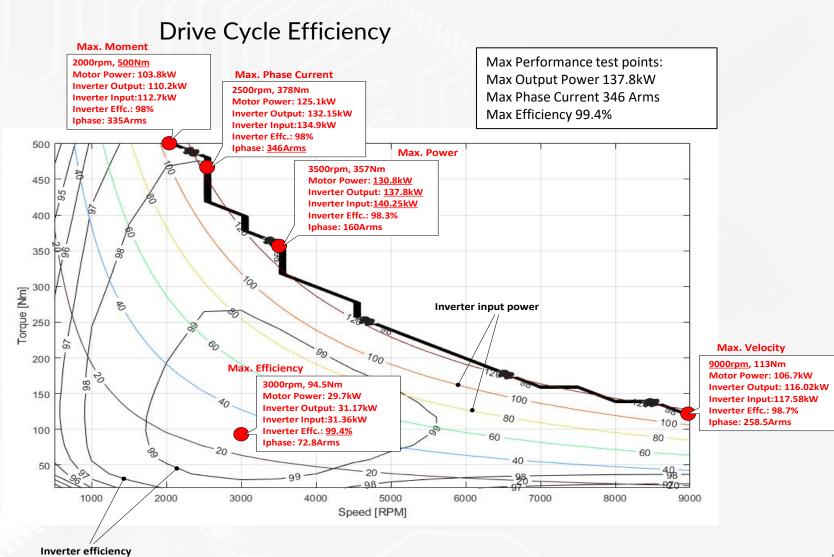


VM022 Module Prototype (by far not optimized module)



VM022 Inverter Power Core



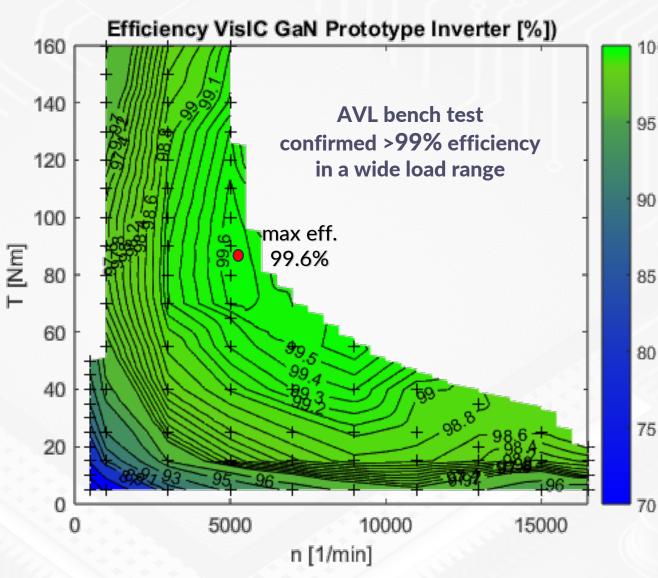


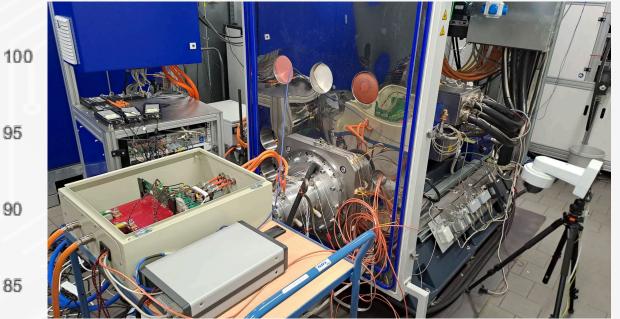
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Oct 2024: Dyno Tests @ AVL Regensburg









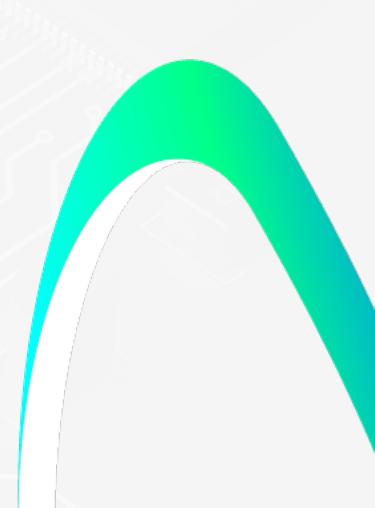
- Max. Efficiency: >99,5%* (400V, 10kHz, 9kmin⁻¹, 55Nm)
- DUT Gen. 1 GaN: latest Generation will improve further Performance and Efficiency
- Max current: 330Arms
- Sensitivity of Switching Frequency (5 14 kHz) have been measured – analysis ongoing

* Value might even be higher – is matter of closer evaluation



Tech Performance is proven

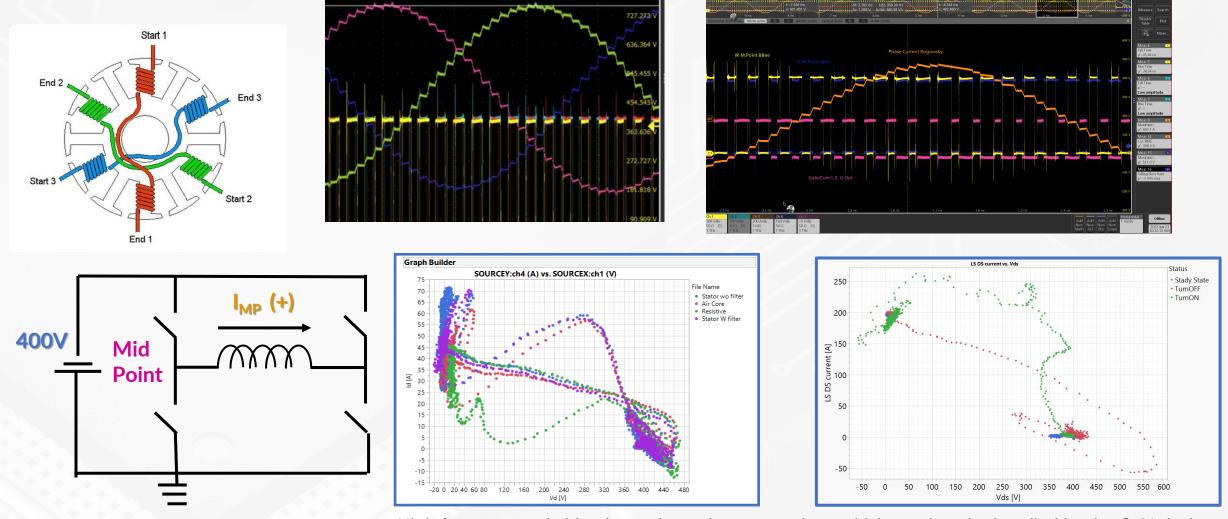
What about robustness & costs?



Transistor Operation in Inverters – hard switching



Sine wave of 800 Hz is generated by high frequency switching of 10 kHz (IGBT) to >25 kHz (SiC, GaN)



High frequency switching is causing voltage over shots which needs to be handled by the GaN devices

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Semi Technology Robustness for Inverter



Gate Breakdown, V



Drain Breakdown, V

D3GaN D3GaN **EGaN EGaN** SIC MOSFET SIC MOSFET Si IGBT Si IGBT 0 500 1000 1500 2000 20 30 50 70 0 10 40 60 Static max rating Drain Vgd Single event Drain Vgd Static max raiting Gate Vgs Single event Gate Vgs

D³GaN - robustness as known from IGBT / SiC is allowing D³GaN to be used in high power inductive applications

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Summary

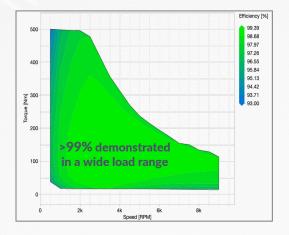


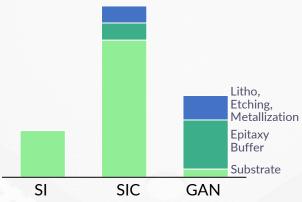
Gate Breakdown, V

EGaN

Si IGBT

SIC MOSFET





- D³GaN provides outstanding inverter efficiency over drive cycle is proven:
 - OEM test bench results
 - AVL test bench results
- Automotive Robustness is given and proven
 - High break down voltages
 - Short Circuit robustness
- EV cost down to realize affordable urban vehicles
 - better inverter efficiency, especially in low load conditions vs SiC
 - reduction of battery size to achieve same driving distances vs IGBT
- D³GaN is the technology implementation to support the requirements of efficient traction inverters and affordable EVs





THANK YOU

